

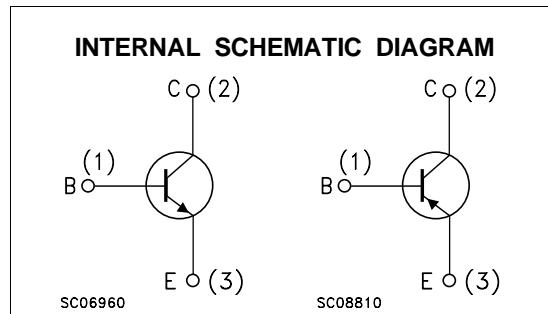
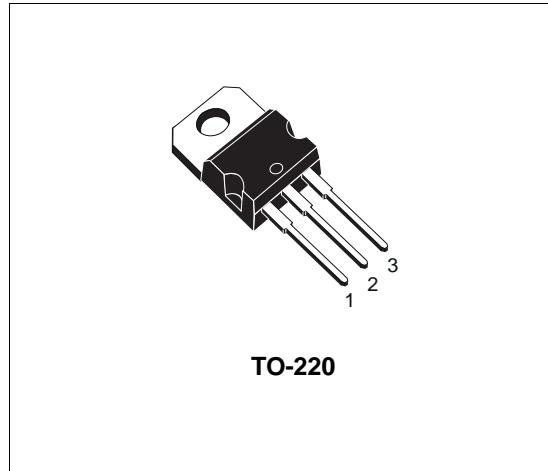
COMPLEMENTARY SILICON POWER TRANSISTORS

- BD534, BD535, BD536, BD537 AND BD538 ARE STMicroelectronics PREFERRED SALESTYPES

DESCRIPTION

The BD533, BD535, and BD537 are silicon Epitaxial-Base NPN power transistors in Jedec TO-220 plastic package, intended for use in medium power linear and switching applications.

The complementary PNP types are BD534, BD536, and BD538 respectively.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		NPN	BD533	BD535	BD537	
	PNP	BD534	BD536	BD538		
V_{CBO}	Collector-Base Voltage ($I_E = 0$)		45	60	80	V
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)		45	60	80	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)		45	60	80	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)			5		V
I_C, I_E	Collector and Emitter Current			8		A
I_B	Base Current			1		A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ\text{C}$			50		W
T_{stg}	Storage Temperature			-65 to 150		$^\circ\text{C}$
T_j	Max. Operating Junction Temperature			150		$^\circ\text{C}$

For PNP types voltage and current values are negative.

BD533 BD534 BD535 DB536 BD537 BD538

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	2.5	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	70	$^{\circ}\text{C}/\text{W}$

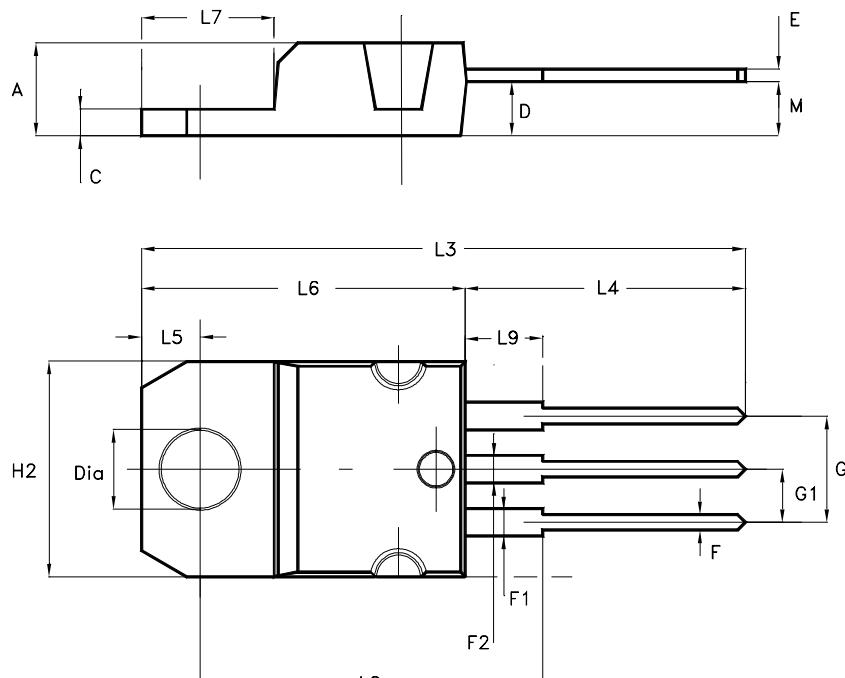
ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions			Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	for BD533/534	$V_{CB} = 45 \text{ V}$				100	μA
		for BD535/536	$V_{CB} = 60 \text{ V}$				100	μA
		for BD537/538	$V_{CB} = 80 \text{ V}$				100	μA
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	for BD533/534	$V_{CE} = 45 \text{ V}$				100	μA
		for BD535/536	$V_{CE} = 60 \text{ V}$				100	μA
		for BD537/538	$V_{CE} = 80 \text{ V}$				100	μA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5 \text{ V}$					1	mA
$V_{CEO(sus)*}$	Collector-Emitter Sustaining Voltage ($I_B = 0$)	$I_C = 100 \text{ mA}$	for BD533/534	45				V
			for BD535/536	60				V
			for BD537/538	80				V
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 2 \text{ A}$	$I_B = 0.2 \text{ A}$			0.8		V
		$I_C = 6 \text{ A}$	$I_B = 0.6 \text{ A}$					V
V_{BE*}	Base-Emitter Voltage	$I_C = 2 \text{ A}$	$V_{CE} = 2 \text{ V}$				1.5	V
h_{FE*}	DC Current Gain	$I_C = 10 \text{ mA}$	$V_{CE} = 5 \text{ V}$		20			
			for BD533/534		20			
			for BD535/536		15			
		$I_C = 500 \text{ mA}$	$V_{CE} = 2 \text{ V}$		40			
		$I_C = 2 \text{ A}$	$V_{CE} = 2 \text{ V}$			25		
			for BD533/534			25		
			for BD535/536			15		
f_T	Transition frequency	$I_C = 500 \text{ mA}$	$V_{CE} = 1 \text{ V}$	3	12			MHz

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %
For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
M		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



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